2-input NAND gate Rev. 04 — 11 July 2007

### 1. General description

The 74HC1G00 and 74HCT1G00 are high speed Si-gate CMOS devices. They provide a 2-input NAND function.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

The standard output currents are half those of the 74HC00 and 74HCT00.

#### 2. Features

- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- SOT353-1 and SOT753 package options

### 3. Ordering information

#### Table 1. Ordering information

Type number	Package						
	Temperature range	Name	Description	Version			
74HC1G00GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads;	SOT353-1			
74HCT1G00GW			body width 1.25 mm				
74HC1G00GV	–40 °C to +125 °C SC-74A		plastic surface-mounted package; 5 leads	SOT753			
74HCT1G00GV							

#### 4. Marking

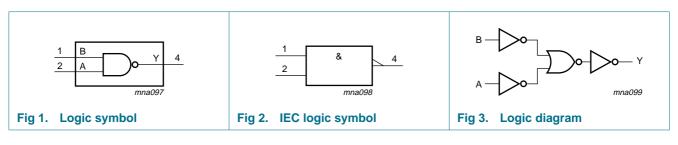
#### Table 2.Marking codes

Type number	Marking
74HC1G00GW	НА
74HCT1G00GW	ТА
74HC1G00GV	H00
74HCT1G00GV	Т00



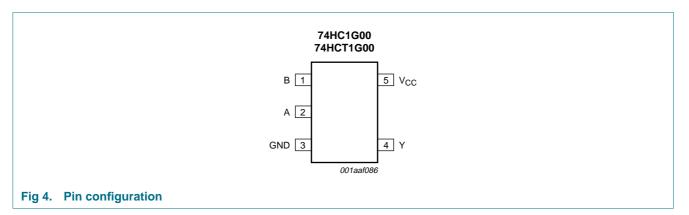
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### 5. Functional diagram



### 6. Pinning information

### 6.1 Pinning



### 6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
В	1	data input
А	2	data input
GND	3	ground (0 V)
Y	4	data output
V <sub>CC</sub>	5	supply voltage

### 7. Functional description

#### Table 4.Function table

*H* = *HIGH* voltage level; *L* = *LOW* voltage level

Input		Output
Α	В	Y
L	L	Н
L	Н	Н
н	L	Н
Н	Н	L

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### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_{I}$ < -0.5 V or $V_{I}$ > $V_{CC}$ + 0.5 V	-	±20	mA
I <sub>OK</sub>	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	-	±20	mA
lo	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±12.5	mA
I <sub>CC</sub>	supply current		-	25	mA
I <sub>GND</sub>	ground current		-25	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$	[2] _	200	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 55 °C the value of  $P_{tot}$  derates linearly with 2.5 mW/K.

### 9. Recommended operating conditions

#### Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	7	74HC1G00			74HCT1G00		
			Min	Тур	Max	Min	Тур	Max	
V <sub>CC</sub>	supply voltage	'	2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
Vo	output voltage		0	-	$V_{CC}$	0	-	$V_{CC}$	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
	and fall rate	$V_{CC} = 4.5 V$	-	-	139	-	-	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

#### **10. Static characteristics**

#### Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb}$  = 25 °C.

0				-					
Symbol	Parameter	Conditions	-40	–40 °C to +85 °C			–40 °C to +125 °C		
			Min	Тур	Max	Min	Max		
For type	74HC1G00								
V <sub>IH</sub>	HIGH-level input	$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	V	
voltage	voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	V	
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	V	
V <sub>IL</sub>	LOW-level input	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	V	
voltage	voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	V	
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	V	

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Symbol	Parameter	Conditions	-40	–40 °C to +85 °C			–40 °C to +125 °C	
			Min	Тур	Max	Min	Max	
V <sub>он</sub>	HIGH-level output	$V_{I} = V_{IH}$ or $V_{IL}$						
	voltage	$I_{O} = -20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.9	2.0	-	1.9	-	V
		$I_{O} = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	V
		$I_{O} = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	5.9	6.0	-	5.9	-	V
		$I_{O}$ = -2.0 mA; $V_{CC}$ = 4.5 V	4.13	4.32	-	3.7	-	V
		$I_{O} = -2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.63	5.81	-	5.2	-	V
V <sub>OL</sub>	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_{O} = 20 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	V
		$I_{O} = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V
		$I_{O} = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	V
		$I_{O}$ = 2.0 mA; $V_{CC}$ = 4.5 V	-	0.15	0.33	-	0.4	V
		$I_{O}$ = 2.6 mA; $V_{CC}$ = 6.0 V	-	0.16	0.33	-	0.4	V
l <sub>i</sub>	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 6.0 V$	-	-	1.0	-	1.0	μΑ
сс	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	10	-	20	μA
Cı	input capacitance		-	1.5	-	-	-	pF
For type	74HCT1G00							
/ <sub>IH</sub>	HIGH-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
VIL	LOW-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
∕ <sub>он</sub>	HIGH-level output	$V_I = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	V
		$I_{O}$ = -2.0 mA; $V_{CC}$ = 4.5 V	4.13	4.32	-	3.7	-	V
∕ <sub>OL</sub>	LOW-level output	$V_I = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_{O} = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V
		$I_{O}$ = 2.0 mA; $V_{CC}$ = 4.5 V	-	0.15	0.33	-	0.4	V
I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	1.0	-	1.0	μΑ
сс	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 5.5 \ V \end{array}$	-	-	10	-	20	μA
2l <sup>CC</sup>	additional supply current	per input; V <sub>CC</sub> = 4.5 V to 5.5 V; V <sub>I</sub> = V <sub>CC</sub> - 2.1 V; I <sub>O</sub> = 0 A	-	-	500	-	850	μA
C <sub>I</sub>	input capacitance		-	1.5	-	-	-	pF

#### Table 7. Static characteristics ... continued

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### **11. Dynamic characteristics**

#### Table 8. Dynamic characteristics

GND = 0 V;  $t_r = t_f \le 6.0$  ns; All typical values are measured at  $T_{amb} = 25 \degree C$ . For test circuit see Figure 6

		21	umo						
Symbol	Parameter	Conditions		–40 °C to +85		5 °C	–40 °C to +125 °C		Unit
			-	Min	Тур	Max	Min	Max	1
For type	74HC1G00	'							
t <sub>pd</sub>	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 2.0 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	25	115	-	135	ns
		$V_{CC} = 4.5 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	9	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	7	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	8	20	-	23	ns
C <sub>PD</sub>	power dissipation capacitance	$V_I = GND$ to $V_{CC}$	[2]	-	19	-	-	-	pF
For type	e 74HCT1G00								
t <sub>pd</sub>	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC} = 4.5 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	12	24	-	27	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	10	-	-	-	ns
C <sub>PD</sub>	power dissipation capacitance	$V_{\rm I}$ = GND to $V_{\rm CC}-$ 1.5 V	[2]	-	21	-	-	-	pF

 $\label{eq:tpd} [1] \quad t_{pd} \text{ is the same as } t_{PLH} \text{ and } t_{PHL}.$ 

[2]  $C_{PD}$  is used to determine the dynamic power dissipation P<sub>D</sub> (µW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o)$  where:

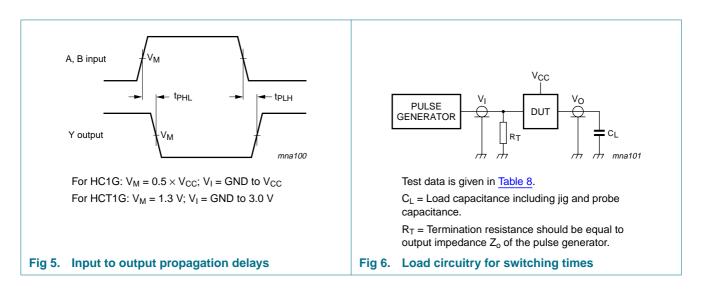
 $f_i$  = input frequency in MHz;  $f_o$  = output frequency in MHz

 $C_L$  = output load capacitance in pF

V<sub>CC</sub> = supply voltage in Volts

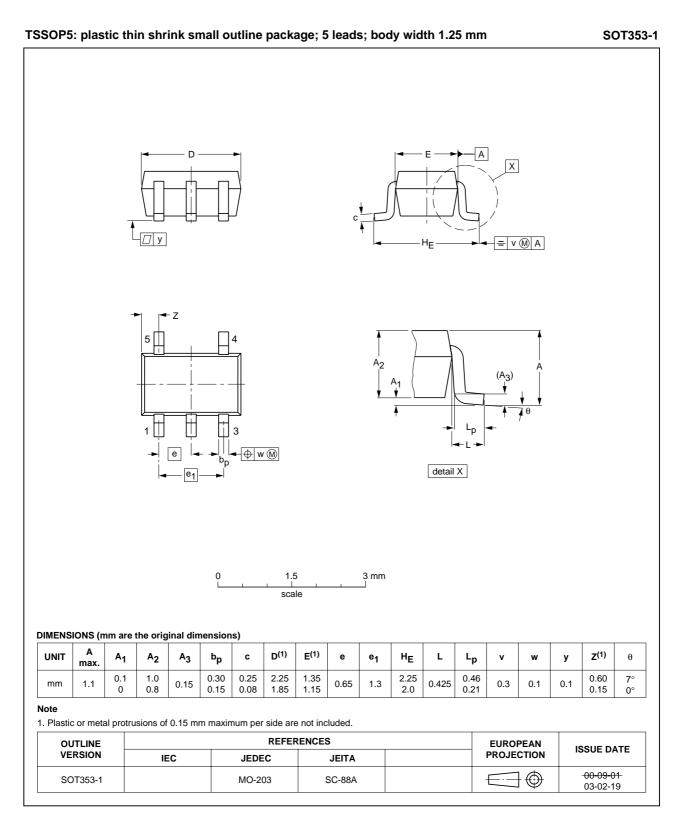
 $\Sigma~(C_L \times V_{CC}{}^2 \times f_o)$  = sum of outputs

### 12. Waveforms



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### 13. Package outline



#### Fig 7. Package outline SOT353-1 (TSSOP5)

2-input NAND gate

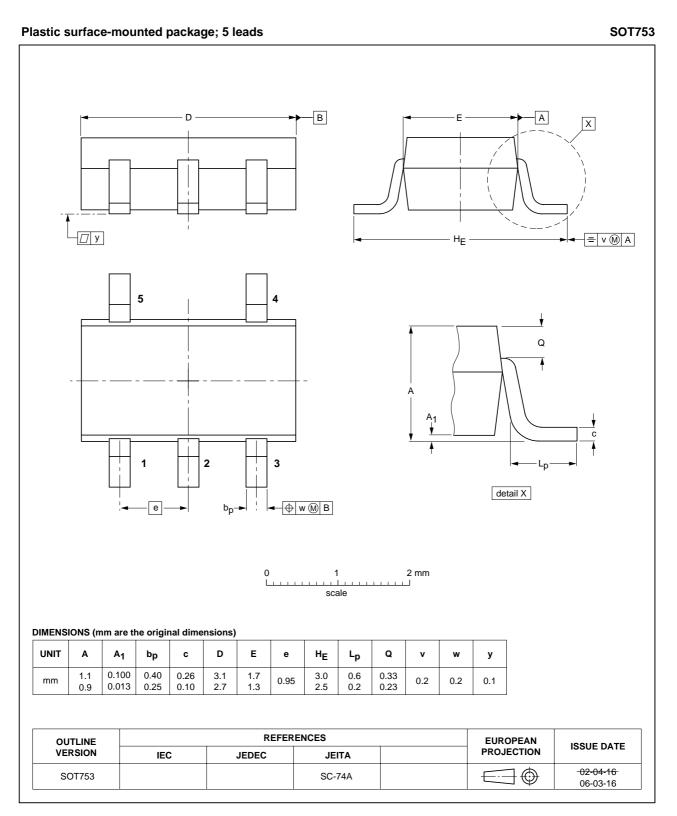


Fig 8. Package outline SOT753 (SC-74A)

### 14. Abbreviations

Table 9.	Abbreviations		
Acronym	Description		
DUT	Device Under Test		
TTL	Transistor-Transistor Logic		

## **15. Revision history**

#### Table 10.Revision history

	-			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT1G00_4	20070711	Product data sheet	-	74HC_HCT1G00_3
Modifications:		t of this data sheet has been re of NXP Semiconductors.	edesigned to comply v	with the new identity
	<ul> <li>Legal texts</li> </ul>	s have been adapted to the ne	w company name whe	ere appropriate.
	<ul> <li>Package S</li> </ul>	OT353 changed to SOT353-1	in Section 3 and Sect	tion 13.
	<ul> <li>Quick refe</li> </ul>	rence data and Soldering sect	ions removed.	
	Section 2	"Features" updated.		
74HC_HCT1G00_3	20020515	Product specification	-	74HC_HCT1G00_2
74HC_HCT1G00_2	20010302	Product specification	-	74HC_HCT1G00_1
74HC_HCT1G00_1	19980730	Preliminary specification	-	-

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#### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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## 74HC1G00; 74HCT1G00

2-input NAND gate

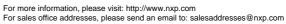
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